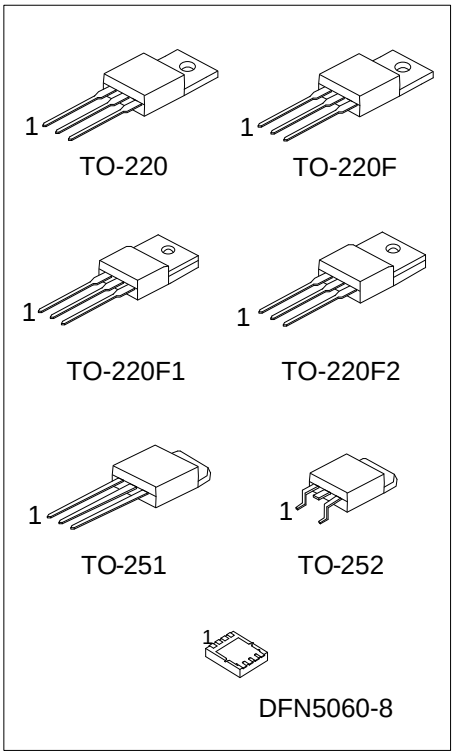
15A, 200V N-CHANNEL POWER MOSFET



■ DESCRIPTION

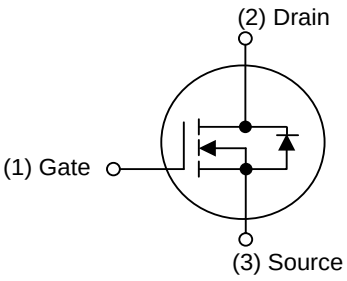
The UTC **15N20** is an N-channel enhancement MOSFET using UTC's advanced technology to provide the customers with perfect $R_{DS(ON)}$, high switching speed, high current capacity and low gate charge.

The UTC **15N20** is universally applied in low voltage such as automotive, high efficiency switching for AC/DC converters and DC motor control, etc.

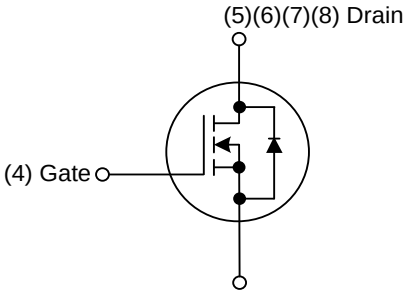
■ FEATURES

* $R_{DS(ON)} \leq 250\ m\Omega$ @ V_{GS}=10V, I_D=7.5A
* High Switching Speed

■ SYMBOL



TO-220/TO-220F/TO-220F1
TO-220F2/TO-251/TO-252

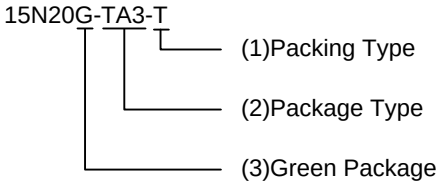


DFN5060-8

■ ORDERING INFORMATION

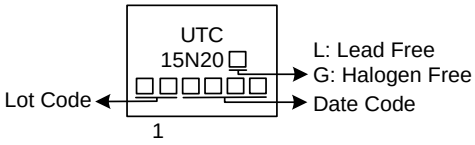
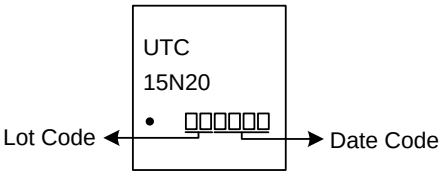
Ordering Number		Package	Pin Assignment								Packing
Lead Free	Halogen Free		1	2	3	4	5	6	7	8	
15N20L-TA3-T	15N20G-TA3-T	TO-220	G	D	S	-	-	-	-	-	Tube
15N20L-TF1-T	15N20G-TF1-T	TO-220F1	G	D	S	-	-	-	-	-	Tube
15N20L-TF2-T	15N20G-TF2-T	TO-220F2	G	D	S	-	-	-	-	-	Tube
15N20L-TF3-T	15N20G-TF3-T	TO-220F	G	D	S	-	-	-	-	-	Tube
15N20L-TM3-T	15N20G-TM3-T	TO-251	G	D	S	-	-	-	-	-	Tube
15N20L-TN3-R	15N20G-TN3-R	TO-252	G	D	S	-	-	-	-	-	Tape Reel
15N20L-K08-5060-R	15N20G-K08-5060-R	DFN5060-8	S	S	S	G	D	D	D	D	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source



(1) T: Tube, R: Tape Reel
(2) TA3: TO-220, TF3: TO-220F, TF1: TO-220F1, TF2: TO-220F2, TM3: TO-251, TN3: TO-252 K08-5060: DFN5060-8
(3) G: Halogen Free and Lead Free, L: Lead Free

■ MARKING

TO-220 / TO-220F / TO-251 / TO-252	DFN5060-8
	

■ ABSOLUTE MAXIMUM RATINGS (T_C=25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	200	V
Gate-Source Voltage		V_{GSS}	±30	V
Continuous Drain Current	Continuous	I_D	15	A
	Pulsed	I_{DM}	60	A
Single Pulsed Avalanche Current		I_{AS}	15	A
Single Pulsed Avalanche Energy		E_{AS}	170	mJ
Power Dissipation	TO-220	P_D	100	W
	TO-220F/TO-220F1 TO-220F2		40	
	TO-251/TO-252		55	
	DFN5060-8		14	
Junction Temperature		T_J	+150	°C
Storage Temperature		T_{STG}	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
2. Repetitive Rating : Pulse width limited by maximum junction temperature.

■ THERMAL DATA

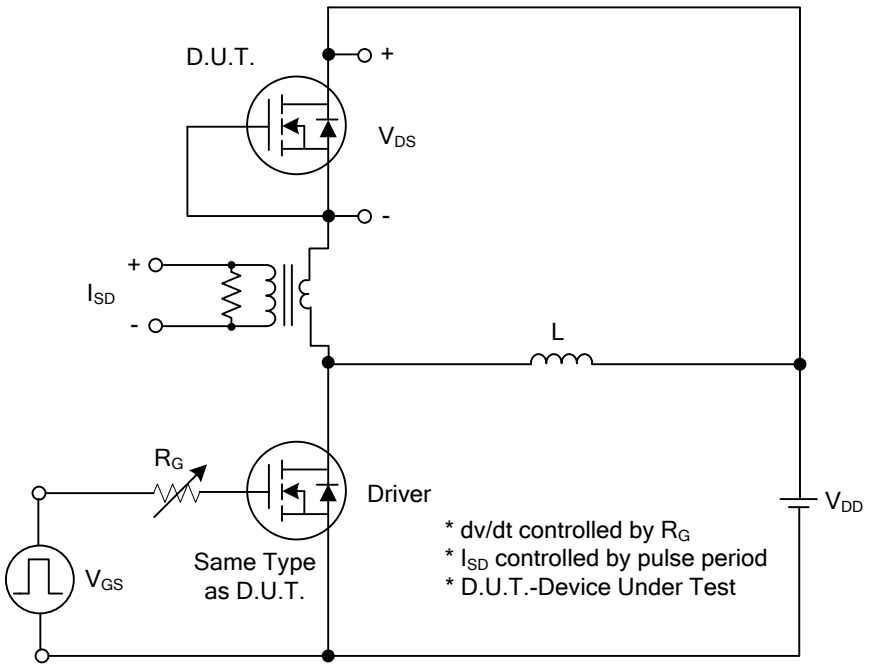
PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient	TO-220/TO-220F TO-220F1/TO-220F2	θ_{JA}	62.5	°C/W
	TO-251/TO-252		110	
	DFN5060-8		65	
Junction to Case	TO-220	θ_{JC}	1	°C/W
	TO-220F/TO-220F1 TO-220F2		3.125 (Note)	
	TO-251/TO-252		2.27 (Note)	
	DFN5060-8		8.92 (Note)	

Note: Device mounted on FR-4 substrate P_C board, 2oz copper, with 1inch square copper plate.

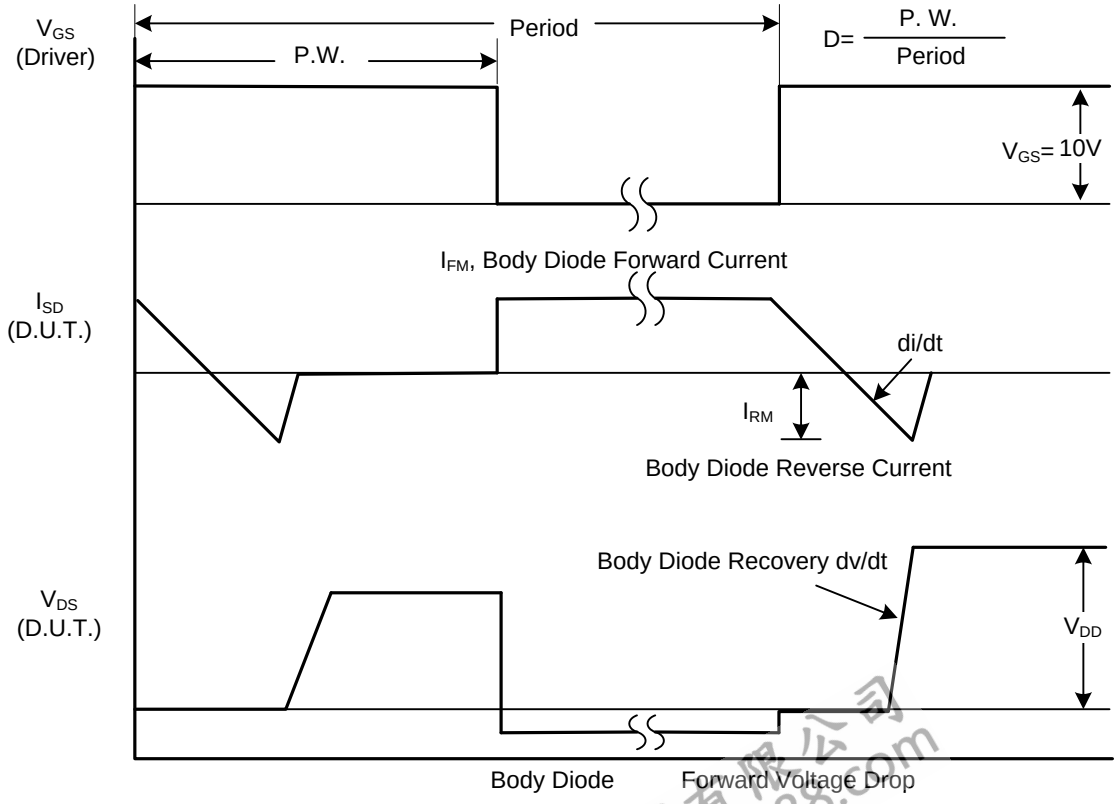
■ ELECTRICAL CHARACTERISTICS

PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV_{DSS}	I_D=250μA, V_{GS}=0V	200			V
Drain-Source Leakage Current		I_{DSS}	V_{DS}=200V, V_{GS}=0V			1	μA
Gate-Source Leakage Current	Forward	I_{GSS}	V_{GS}=+30V, V_{DS}=0V			+100	nA
	Reverse		V_{GS}=-30V, V_{DS}=0V			-100	nA
ON CHARACTERISTICS							
Gate Threshold Voltage		$V_{GS(TH)}$	V_{DS}=V_{GS}, I_D=250μA	2.0		4.0	V
Static Drain-Source On-State Resistance		$R_{DS(ON)}$	V_{GS}=10V, I_D=7.5A		200	250	mΩ
DYNAMIC PARAMETERS							
Input Capacitance		C_{ISS}	V_{GS}=0V, V_{DS}=25V, f=1.0MHz		610	800	pF
Output Capacitance		C_{OSS}			145	200	pF
Reverse Transfer Capacitance		C_{RSS}			28	40	pF
SWITCHING PARAMETERS							
Total Gate Charge		Q_G	V_{GS}=10V, V_{DD}=100V, I_D=15A		21		nC
Gate to Source Charge		Q_{GS}			4.6		nC
Gate to Drain Charge		Q_{GD}			7		nC
Turn-ON Delay Time		$t_{D(ON)}$	V_{DD}=100V, I_D=15A, R_G=25Ω, V_{GS}=10V		9.6		ns
Rise Time		t_R			20		ns
Turn-OFF Delay Time		$t_{D(OFF)}$			53		ns
Fall-Time		t_F			23		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS							
Maximum Body-Diode Continuous Current		I_S				15	A
Maximum Body-Diode Pulsed Current		I_{SM}				60	A
Drain-Source Diode Forward Voltage		V_{SD}	I_S=15A, V_{GS}=0V			1.5	V
Reverse Recovery Time (Note 1)		t_{rr}	I_S=15A , V_{GS}=0V, di/dt=100A/μs		220		ns
Reverse Recovery Charge		Q_{rr}			2.5		μC

■ TEST CIRCUITS AND WAVEFORMS

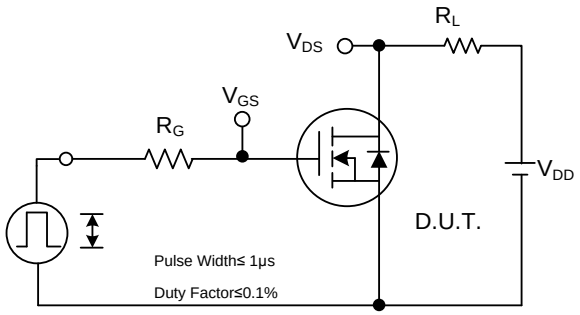


Peak Diode Recovery dv/dt Test Circuit

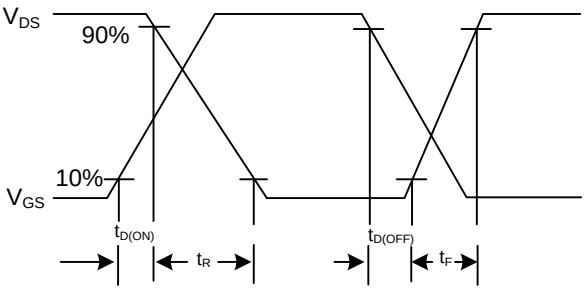


Peak Diode Recovery dv/dt Waveforms

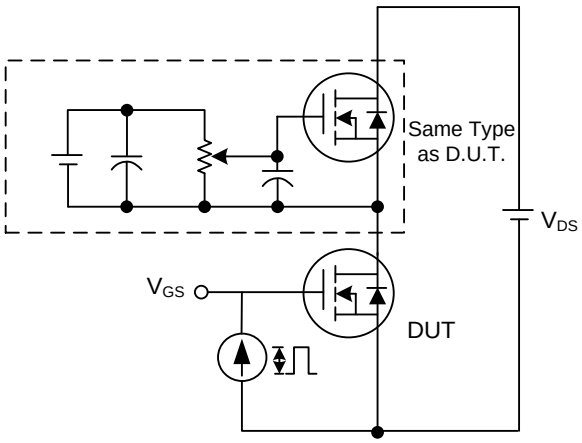
■ TEST CIRCUITS AND WAVEFORMS



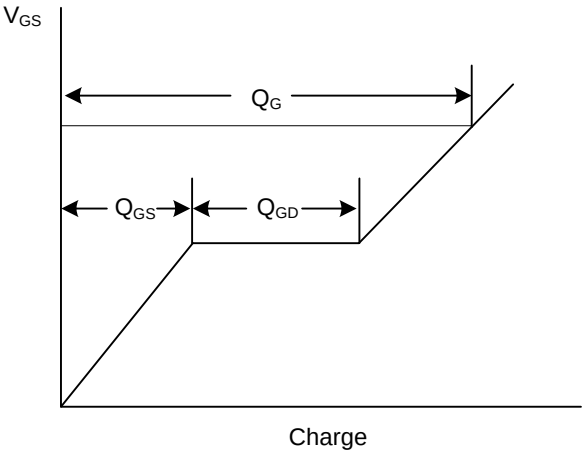
Switching Test Circuit



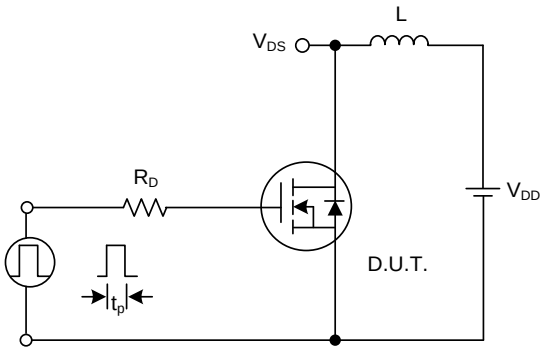
Switching Waveforms



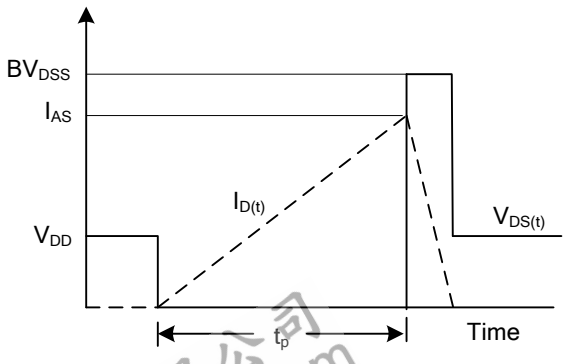
Gate Charge Test Circuit



Gate Charge Waveform



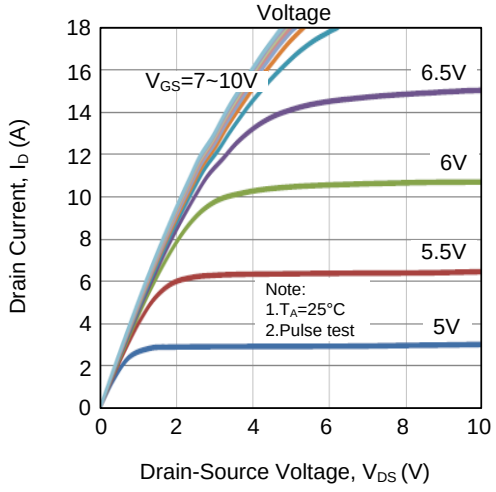
Unclamped Inductive Switching Test Circuit



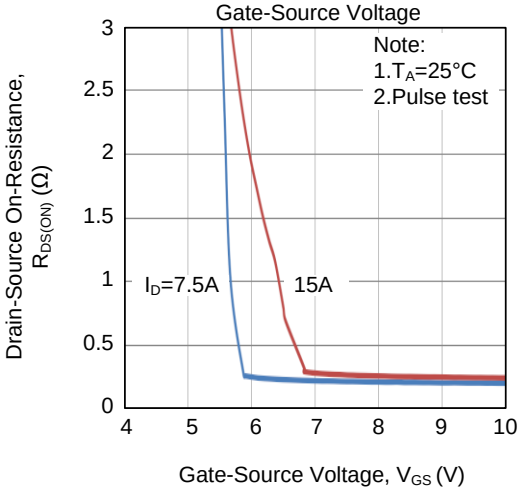
Unclamped Inductive Switching Waveforms

■ TYPICAL CHARACTERISTICS

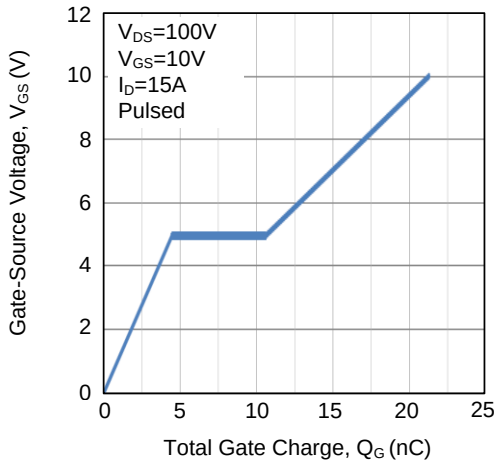
Drain Current vs. Drain-Source Voltage



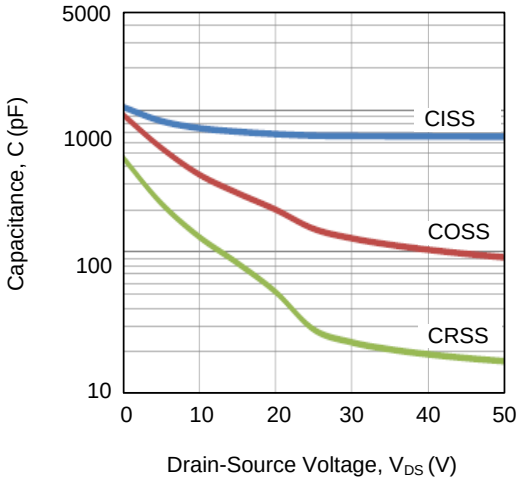
Drain-Source On-Resistance vs. Gate-Source Voltage



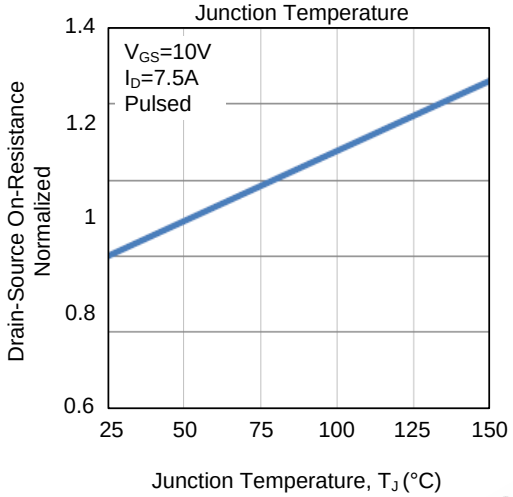
Gate Charge Characteristics



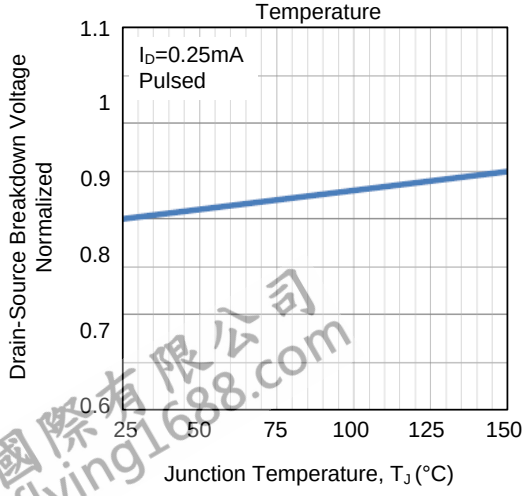
Capacitance Characteristics



Drain-Source On-Resistance vs. Junction Temperature

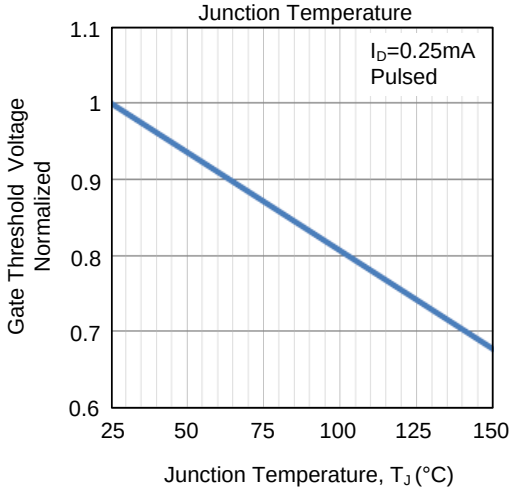


Breakdown Voltage vs. Junction Temperature

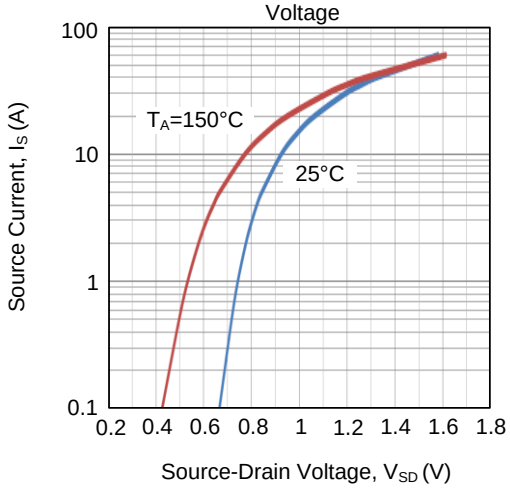


■ TYPICAL CHARACTERISTICS (Cont.)

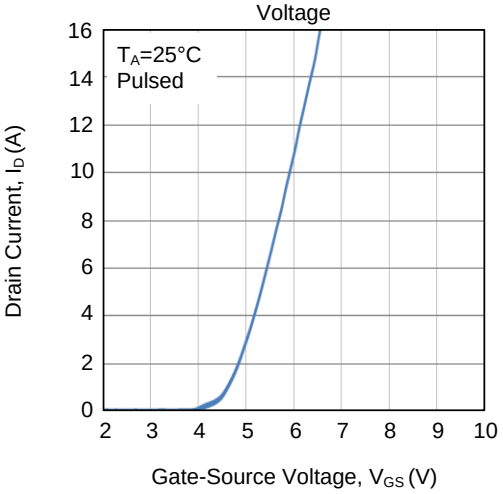
Gate Threshold Voltage vs. Junction Temperature



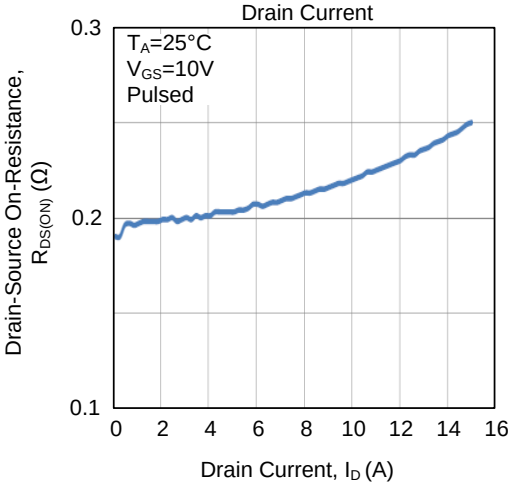
Source Current vs. Source-Drain Voltage



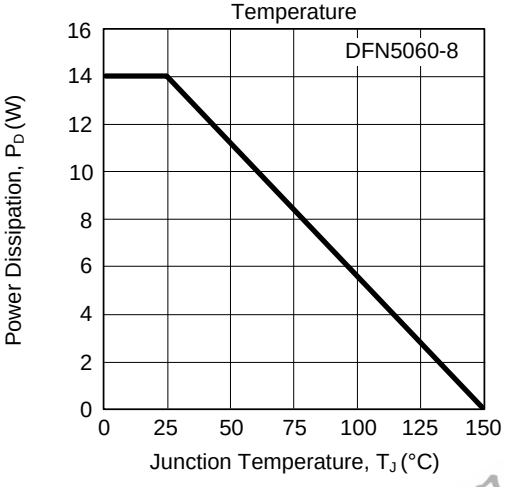
Drain Current vs. Gate-Source Voltage



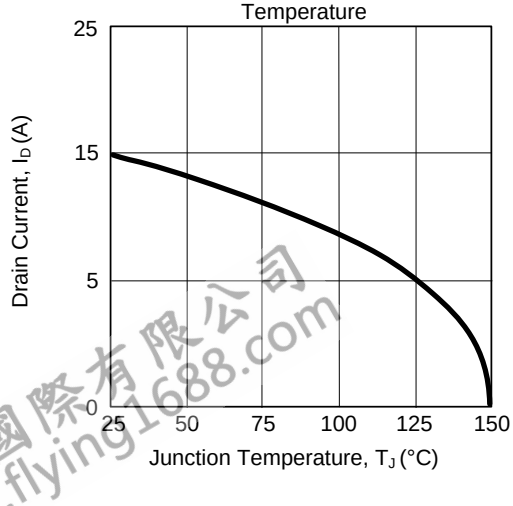
Drain-Source On-Resistance vs. Drain Current



Power Dissipation vs. Junction Temperature



Drain Current vs. Junction Temperature



■ TYPICAL CHARACTERISTICS (Cont.)